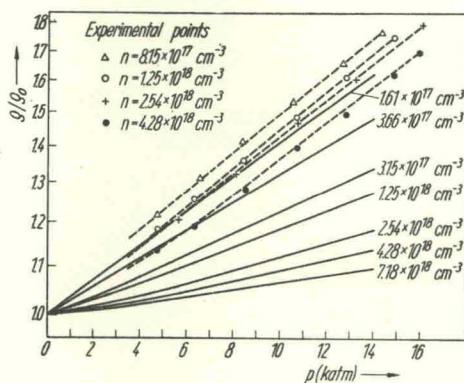


Fig. 2. Dependence of resistivity on pressure; solid lines - theoretical

It is worth mentioning that the same disagreement was observed in n-type HgTe where negative $d\alpha/dp$ observed for pure samples change sign for heavily doped ones (6).

The theory of scattering processes which gives good agreement in the case of pure material cannot be used directly for a heavily doped one.



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